

AMENDMENTS TO THE SPECIFICATION

Please amend the current title with the following new title:

**METHOD OF FORMING CMOS IMAGER PIXELS WITH CAPACITOR
STRUCTURES**

Please amend the specification as follows:

[0059] As illustrated in FIG. 10, storage capacitor 199 is formed entirely over upper surface 115a of the field oxide region 115 and within lateral boundaries 115b₁, 115b₂. Although the above embodiment was described with reference to the formation of the storage capacitor 199 entirely overlying the field oxide region 115, the invention also contemplates the formation of a storage capacitor formed entirely overlying an active area of a pixel sensor cell. For example, FIG. 11 illustrates storage capacitor 199a formed entirely over the active area A of the pixel sensor cell 100.